

## Supporting Information

# High-Performance $\epsilon$ -Ga<sub>2</sub>O<sub>3</sub> Solar-Blind Photodetectors Grown by MOCVD with Post-Thermal Annealing

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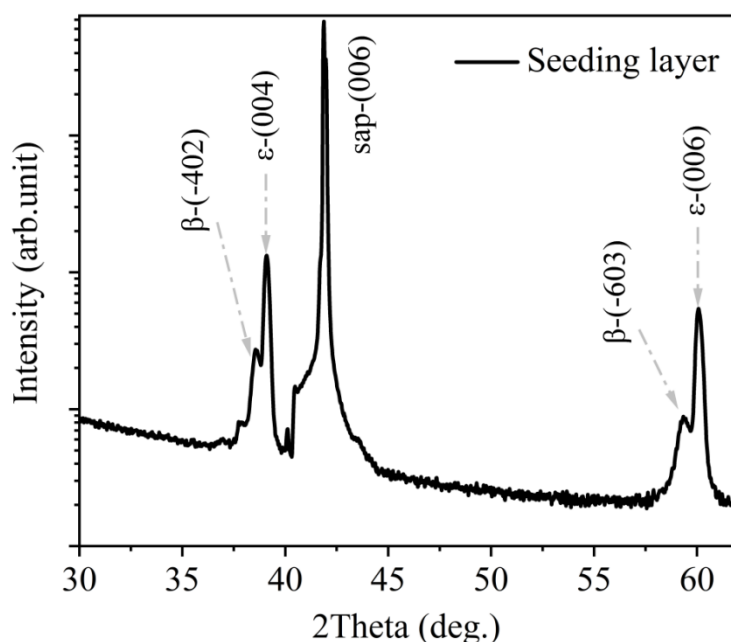


Figure S1. XRD patterns of the  $\epsilon$ -Ga<sub>2</sub>O<sub>3</sub> seeding layer growth on c-plane sapphire